

CD40107B Types

CMOS Dual 2-Input NAND Buffer/Driver

High-Voltage Type (20-Volt Rating)

The RCA-CD40107B is a dual 2-input NAND buffer/driver containing two independent 2-input NAND buffers with open-drain single n-channel transistor outputs. This device features a wired-OR capability and high output sink current capability (136 mA typ. at $V_{DD} = 10\text{ V}$, $V_{DS} = 1\text{ V}$). The CD40107B is supplied in the 8-lead dual-in-line plastic (Mini-DIP) package (E suffix), 14-lead hermetic frit-seal ceramic package (F suffix), and in chip form (H suffix).

Features:

- 32 times standard B-Series output current drive sinking capability — 136 mA typ. @ $V_{DD} = 10\text{ V}$, $V_{DS} = 1\text{ V}$
- 100% tested for quiescent current at 20 V
- Maximum input current of $1\text{ }\mu\text{A}$ at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Noise margin, full package temperature range, R_L to $V_{DD} = 10\text{ k}\Omega$:
 - 1 V at $V_{DD} = 5\text{ V}$
 - 2 V at $V_{DD} = 10\text{ V}$
 - 2.5 V at $V_{DD} = 15\text{ V}$
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"

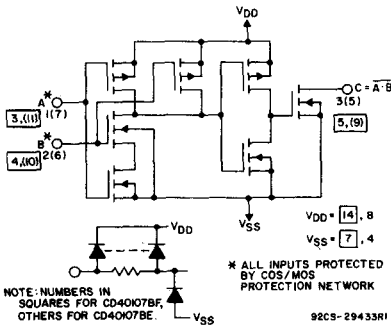
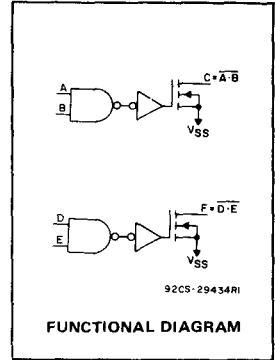


Fig. 1 — Schematic diagram of CD40107B (one of 2 gates)

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) (Voltages referenced to V_{SS} Terminal)	-0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5 to $V_{DD} + 0.5\text{ V}$
DC INPUT CURRENT, ANY ONE INPUT	$\pm 10\text{ mA}$
POWER DISSIPATION PER PACKAGE (P_D)	500 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR:	
For $T_A = -40$ to $+62.5^\circ\text{C}$ (PACKAGE TYPE E)	250 mW
For $T_A = +62.5$ to $+85^\circ\text{C}$ (PACKAGE TYPE E)	Derate Linearly at $8\text{ mW}/^\circ\text{C}$ to 156 mW
For $T_A = -55$ to $+87.5^\circ\text{C}$ (PACKAGE TYPES F, H)	250 mW
For $T_A = +87.5$ to $+125^\circ\text{C}$ (PACKAGE TYPES F, H)	Derate Linearly at $8\text{ mW}/^\circ\text{C}$ to 94 mW
OPERATING-TEMPERATURE RANGE (T_A):	
PACKAGE TYPES F, H	-55 to $+125^\circ\text{C}$
PACKAGE TYPE E	-40 to $+85^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})	-65 to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ inch ($1.59 \pm 0.79\text{ mm}$) from case for 10 s max.	$+265^\circ\text{C}$

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For $T_A =$ Full Package-Temperature Range)	3	18	V

TRUTH TABLE

A	B	C
0	0	1*
1	0	1*
0	1	1*
1	1	0

*Requires external pull-up resistor (R_L) to V_{DD} .

#Without pull-up resistor (3-state).

Applications

- Driving relays, lamps, LEDs
- Line driver
- Level shifter (up or down)

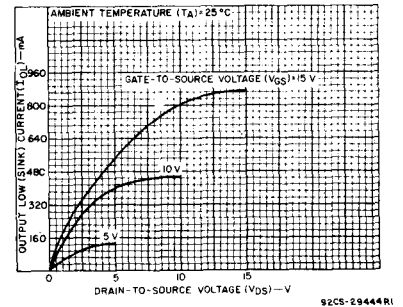


Fig. 2 — Typical output low (sink) current characteristics.

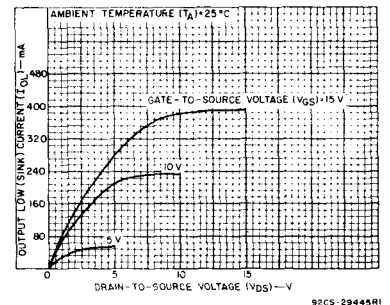


Fig. 3 — Minimum output low (sink) current characteristics.

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DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$, $C_L = 50\text{ pF}$, Input $t_r, t_f = 20\text{ ns}$

CHARACTERISTIC	TEST CONDITIONS	LIMITS		UNITS
		V _{DD} Volts	Typ. Max.	
Propagation Delay: High-to-Low, t_{PHL}	$R_L^* = 120\ \Omega$	5	100 200	ns
		10	45 90	
		15	30 60	
Low-to-High, t_{PLH}	$R_L^* = 120\ \Omega$	5	100 200	ns
		10	60 120	
		15	50 100	
Transition Time: High-to-Low, t_{THL}	$R_L^* = 120\ \Omega$	5	50 100	ns
		10	20 40	
		15	10 20	
Low-to-High, t_{TLH}	$R_L^* = 120\ \Omega$	5	50 100	ns
		10	35 70	
		15	25 50	
Average Input Capacitance, C_{IN}	Any Input	5	7.5	pF
Average Output Capacitance, C_{OUT}	Any Output	30	-	pF

* R_L is external pull-up resistor to V_{DD} .

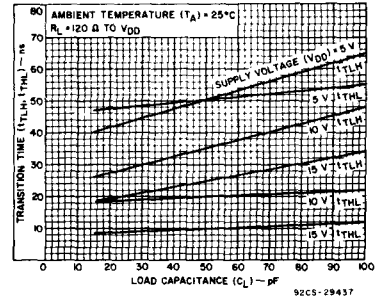


Fig. 4 – Typical transition time as a function of load capacitance.

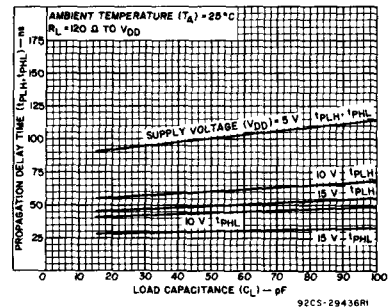


Fig. 5 – Typical propagation delay time as a function of load capacitance.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES ($^\circ\text{C}$)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	Values at $-55, +25, +125$ Apply to F, H Packages Values at $-40, +25, +85$ Apply to E Package							
				-55	-40	+85	+125	+25			
Quiescent Device Current I_{DD} Max.	-	0.5	5	1	1	30	30	-	0.02	1	μA
	-	0.10	10	2	2	60	60	-	0.02	2	
	-	0.15	15	4	4	120	120	-	0.02	4	
	-	0.20	20	20	20	600	600	-	0.04	20	
Output Low (Sink) Current I_{OL} Min.	0.4	0.5	5	21	20	14	12	16	32	-	mA
	1	0.5	5	44	42	30	25	34	68	-	
	0.5	0.10	10	49	46	32	28	37	74	-	
	1	0.10	10	89	85	60	51	68	136	-	
	0.5	0.15	15	66	63	44	38	50	100	-	
Output High (Source) Current I_{OH} Min.	No Internal Pull-Up Device										
Input Low Voltage V_{IL} Max.*	4.5	-	5			1.5				1.5	V
	9	-	10			3				3	
	13.5	-	15			4				4	
Input High Voltage V_{IH} Min.*	0.5, 4.5	-	5			3.5		3.5	-	-	
	1.9	-	10			7		7	-	-	
	1.5, 13.5	-	15			11		11	-	-	
Input Current I_{IJN} Max.	-	0.18	18	± 0.1	± 0.1	± 1	± 1	-	$\pm 10^{-5}$	± 0.1	μA
Output Leakage Current I_{OZ} Max.	18	0.18	18	2	2	20	20	-	10^{-4}	2	μA

* Measured with external pull-up resistor, $R_L = 10\text{ k}\Omega$ to V_{DD} .

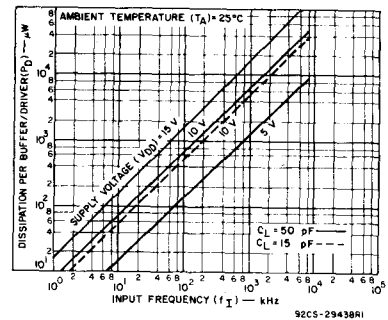


Fig. 6 – Typical power dissipation as a function of input frequency.

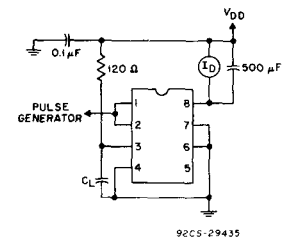
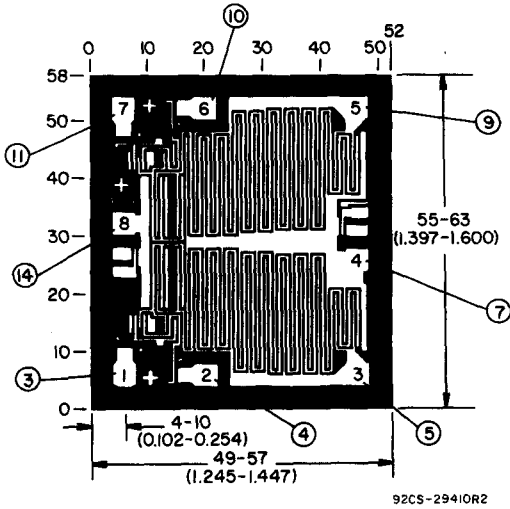


Fig. 7 – Power-dissipation test circuit for CD40107BE.

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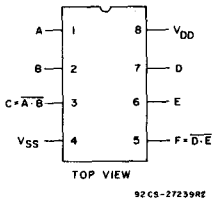


NOTE: NOS. IN PADS FOR CD40107BE
NOS. OUTSIDE CHIP FOR CD40107BF

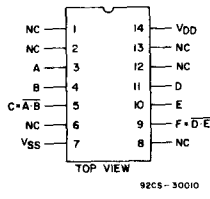
Dimensions and Pad Layout for CD40107BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of ± 3 mils to ± 16 mils applicable to the nominal dimensions shown.



CD40107BE



CD40107BF

TERMINAL ASSIGNMENTS

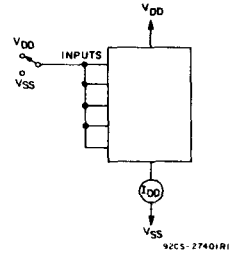


Fig. 8 - Quiescent-device current test circuit.

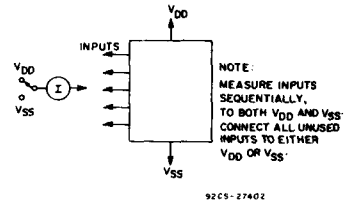
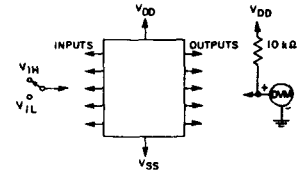


Fig. 9 - Input-current test circuit.



NOTE: TEST ANY COMBINATION OF INPUTS

Fig. 10 - Input-voltage test circuit.

Special Considerations for CD40107B

1. Limiting Capacitive Currents for $C_L > 500$ pF, $V_{DD} > 15$ V.

For $V_{DD} > 15$ V, and load capacitance (C_L) from output to ground > 500 pF, an external 25Ω series limiting resistor should be inserted between the output terminal and C_L . No external resistor is necessary if $C_L < 500$ pF or $V_{DD} < 15$ V.

2. Driving Inductive Loads

When using the CD40107B to drive inductive loads, the load should be shunted with a diode to prevent high voltages from developing across the CD40107B output.